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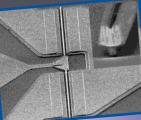
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-ICSCRM-2005-

International Conference on Silicon Carbide and Related Materials

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Semiconductor materials science and technology have provided a solid foundation for the remarkable performance of current electronic and optical device technology. Wide bandgap semiconductors—typically defined as materials exhibiting an electronic bandgap greater than 2.0 eV—are emerging as materials capable of driving continued device performance enhancements for many years to come. Silicon Carbide (SiC) has been studied for decades, but recent development has firmly established commercial products in optical, RF and power components. Continued research in the field will assure that the rapid developmental timeline for SiC-based device technology can continue into the future. The International Conference on Silicon Carbide and Related Materials (ICSCRM '05) will be held September 18-23, 2005, at the Westin Hotel and Convention Center, in Pittsburgh, Pennsylvania (USA). This conference has become the pre-eminent forum to discuss new research results, and assess the true "state of the art" for SiC, as well as gallium nitride (GaN) and other related wide bandgap semiconductors – spanning the entire spectrum from fundamental science of materials through device performance. Abstracts are solicited in the following broad topic areas: Materials Growth (Bulk and Epitaxial), Materials Characterization and Theory, Device Processing and Device Optimization/Performance.



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